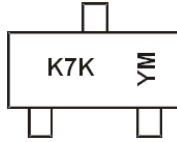


Marking Information



K7K = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: I = 2021)
 M or \bar{M} = Month (ex: 9 = September)

Date Code Key

Year	2006	...	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	T	...	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	380 300	mA
	t < 5s	T _A = +25°C T _A = +70°C	I _D	430 340	mA
Continuous Drain Current (Note 6) V _{GS} = 5V	Steady State	T _A = +25°C T _A = +70°C	I _D	310 240	mA
	t < 5s	T _A = +25°C T _A = +70°C	I _D	350 270	mA
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	0.5	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%) (Note 6)			I _{DM}	1.2	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P _D	370	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	357	°C/W
	t < 5s		292	
Total Power Dissipation (Note 6)		P _D	540	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	240	°C/W
	t < 5s		197	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	91	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. copper, single sided.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	1.6	2.5	V	V _{DS} = 10V, I _D = 1mA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.2	2.0	Ω	V _{GS} = 10V, I _D = 0.5A
			1.4	3.0		V _{GS} = 5V, I _D = 0.05A
Forward Transfer Admittance	Y _{fs}	80	—	—	ms	V _{DS} = 10V, I _D = 0.2A
Diode Forward Voltage	V _{SD}	—	0.75	1.1	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	30	50	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	4.2	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	2.9	5.0	pF	
Gate Resistance	R _g	—	133	—	Ω	f = 1MHz, V _{GS} = 0V, V _{DS} = 0V
Total Gate Charge	Q _g	—	0.3	—	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 250mA
Gate-Source Charge	Q _{gs}	—	0.2	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.08	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	3.9	—	ns	V _{DD} = 30V, V _{GS} = 10V, R _G = 25Ω, I _D = 200mA
Turn-On Rise Time	t _R	—	3.4	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	15.7	—	ns	
Turn-Off Fall Time	t _F	—	9.9	—	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

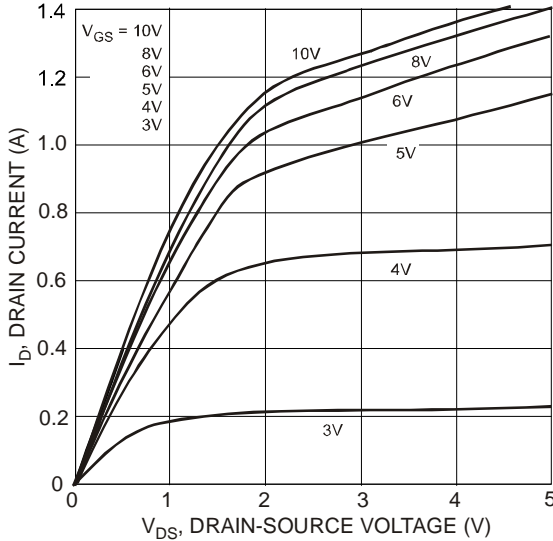


Fig. 1 Typical Output Characteristics

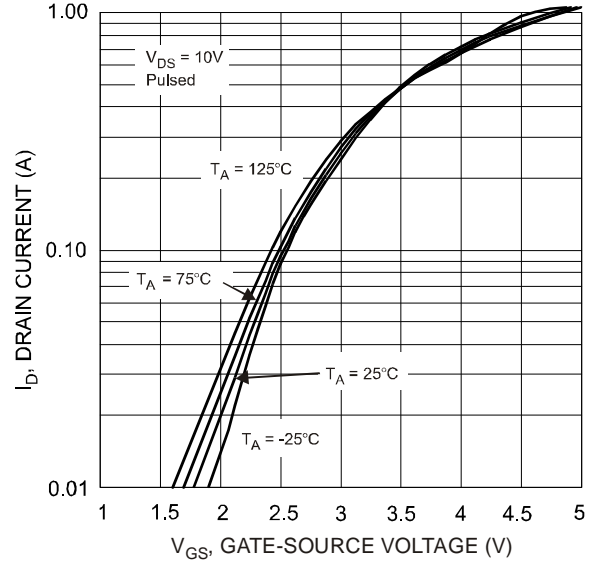


Fig. 2 Typical Transfer Characteristics

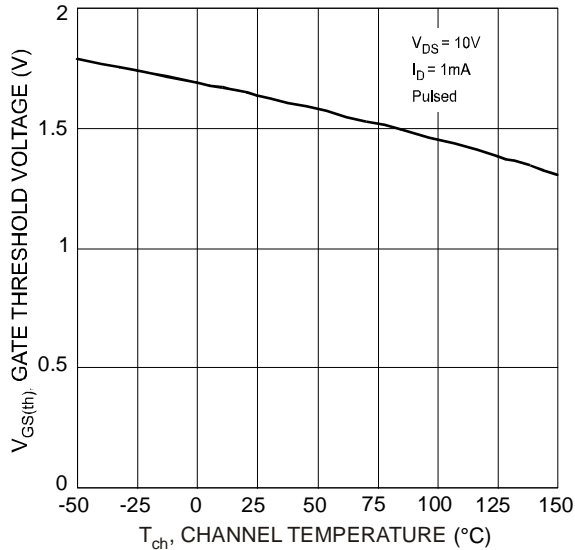


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

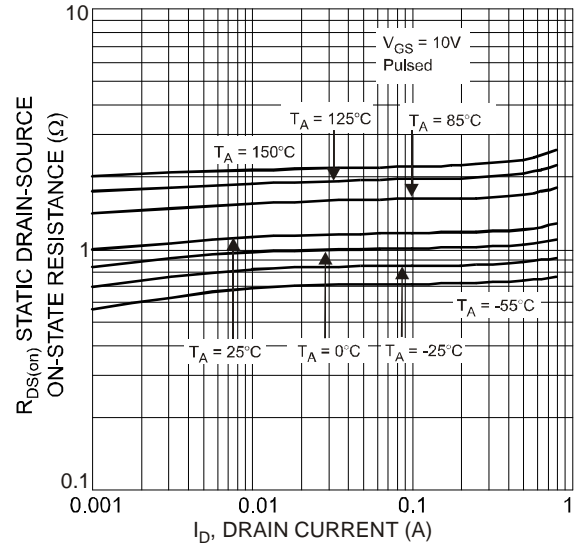


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

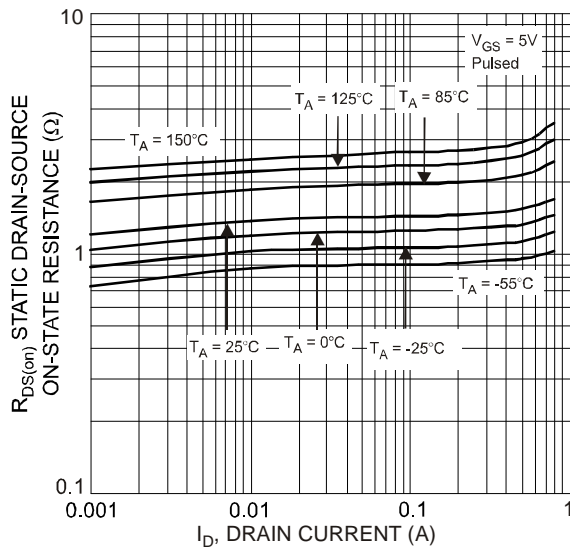


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

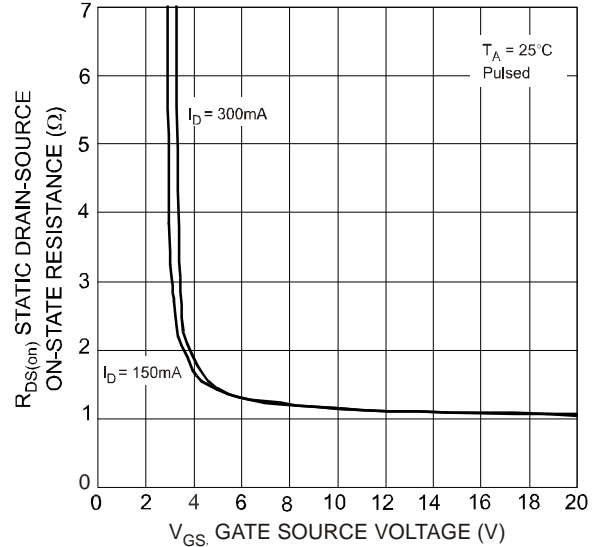


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

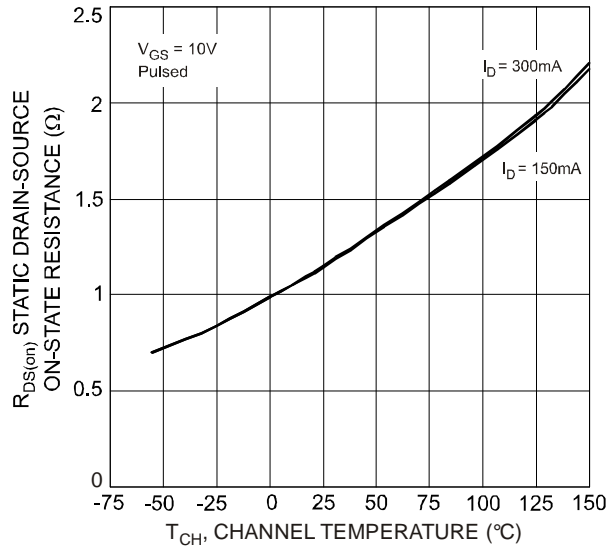


Fig. 7 Static Drain-Source On-State Resistance vs. Channel Temperature

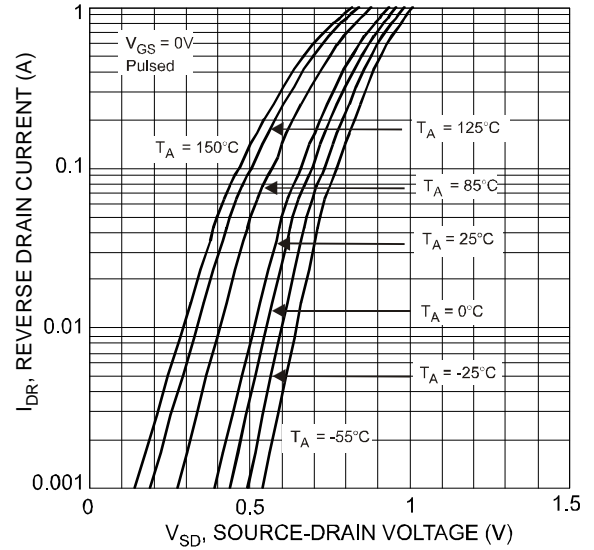


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

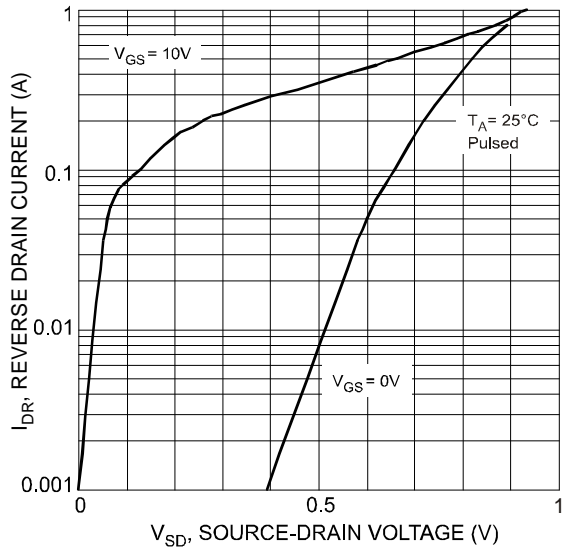


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

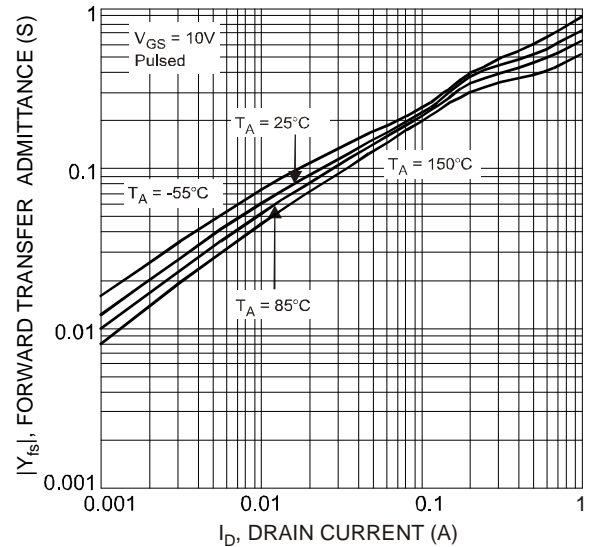


Fig. 10 Forward Transfer Admittance vs. Drain Current

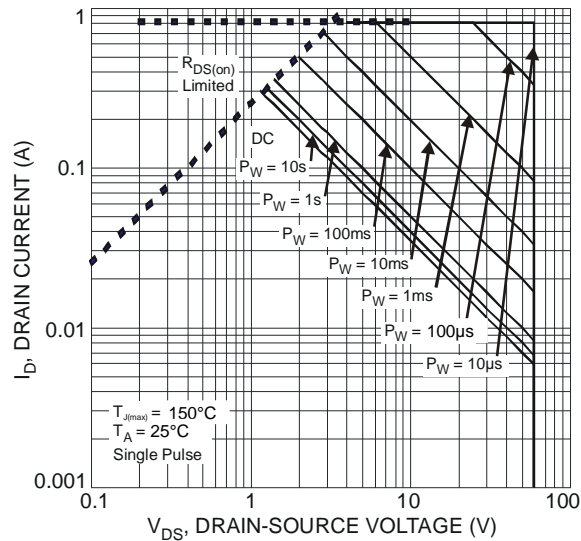


Fig. 11 Safe Operation Area

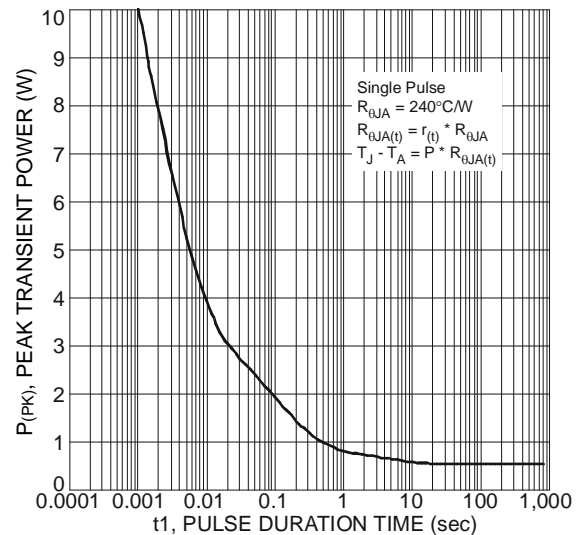


Fig. 12 Single Pulse Maximum Power Dissipation

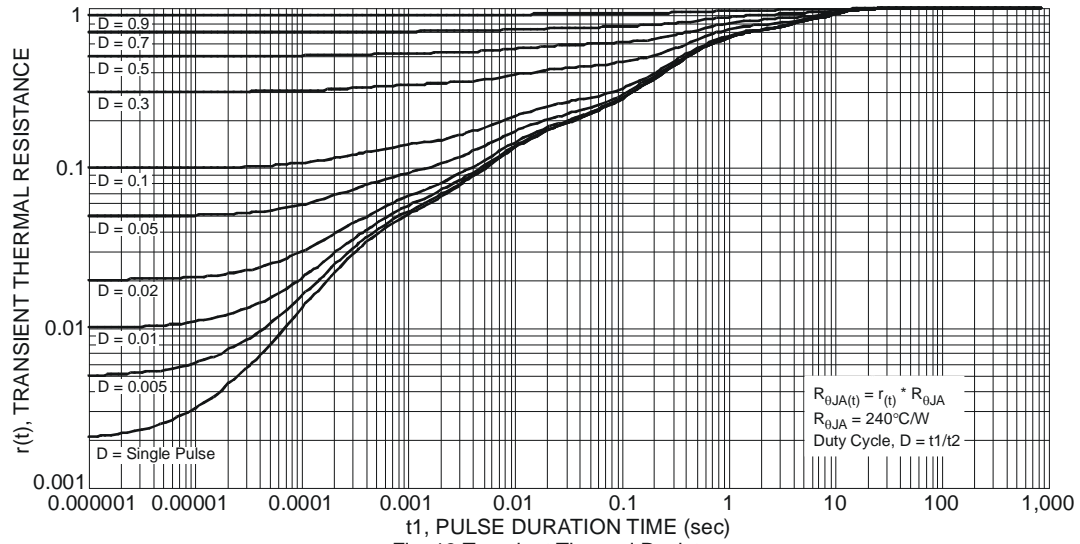
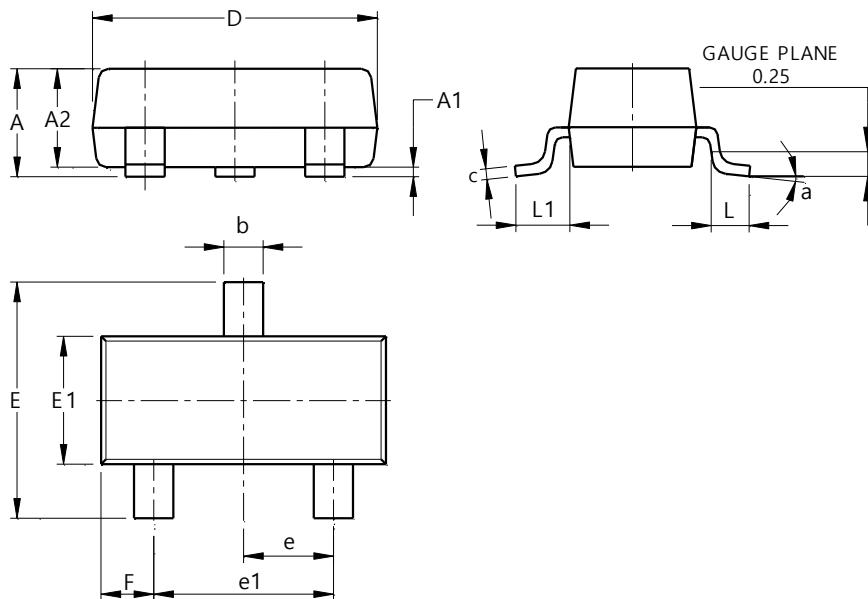


Fig. 13 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23 (Standard)

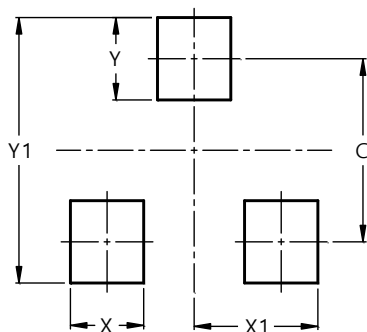


SOT23 (Standard)			
Dim	Min	Max	Typ
A	0.90	1.15	1.025
A1	0.00	0.10	0.05
A2	0.85	1.10	0.975
b	0.30	0.51	0.40
c	0.080	0.202	0.11
D	2.80	3.00	2.90
E	2.25	2.55	2.40
E1	1.20	1.40	1.30
e	0.89	1.03	0.915
e1	1.78	2.05	1.83
F	0.40	0.60	0.535
L1	0.45	0.61	0.55
L	0.25	0.55	0.40
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23 (Standard)



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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